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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	HCS12
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, I²C, SCI, SPI
Peripherals	PWM, WDT
Number of I/O	59
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2.35V ~ 5.25V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-QFP
Supplier Device Package	80-QFP (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s12dg256ccfu

1.6 Detailed Register Map

The following tables show the detailed register map of the MC9S12DP256B.

$0000 - $000F MEBI map 1 of 3 (Core User Guide)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
$0000	PORTA	Read:	Bit 7	6	5	4	3	2	1	Bit 0
		Write:								
$0001	PORTB	Read:	Bit 7	6	5	4	3	2	1	Bit 0
		Write:								
$0002	DDRA	Read:	Bit 7	6	5	4	3	2	1	Bit 0
		Write:								
$0003	DDRB	Read:	Bit 7	6	5	4	3	2	1	Bit 0
		Write:								
$0004	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								
$0005	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								
$0006	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								
$0007	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								
$0008	PORTE	Read:	Bit 7	6	5	4	3	2	Bit 1	Bit 0
		Write:								
$0009	DDRE	Read:	Bit 7	6	5	4	3	Bit 2	0	0
		Write:								
$000A	PEAR	Read:	NOACCE	0	PIPOE	NECLK	LSTRE	RDWE	0	0
		Write:								
$000B	MODE	Read:	MODC	MODB	MODA	0	IVIS	0	EMK	EME
		Write:								
$000C	PUCR	Read:	PUPKE	0	0	PUPEE	0	0	PUPBE	PUPAE
		Write:								
$000D	RDRIV	Read:	RDPK	0	0	RDPE	0	0	RDPB	RDPA
		Write:								
$000E	EBICTL	Read:	0	0	0	0	0	0	0	ESTR
		Write:								
$000F	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								

$0010 - $0014 MMC map 1 of 4 (Core User Guide)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
$0010	INITRM	Read:	RAM15	RAM14	RAM13	RAM12	RAM11	0	0	RAMHAL
		Write:								
$0011	INITRG	Read:	0	REG14	REG13	REG12	REG11	0	0	0
		Write:								

$01C0 - $01FF CAN2 (Motorola Scalable CAN - MSCAN)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
$01CD	Reserved	Read:	0	0	0	0	0	0	0	0
		Write:								
$01CE	CAN2RXERR	Read:	RXERR7	RXERR6	RXERR5	RXERR4	RXERR3	RXERR2	RXERR1	RXERR0
		Write:								
$01CF	CAN2TXERR	Read:	TXERR7	TXERR6	TXERR5	TXERR4	TXERR3	TXERR2	TXERR1	TXERR0
		Write:								
$01D0	CAN2IDAR0	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01D1	CAN2IDAR1	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01D2	CAN2IDAR2	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01D3	CAN2IDAR3	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01D4	CAN2IDMR0	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01D5	CAN2IDMR1	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01D6	CAN2IDMR2	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01D7	CAN2IDMR3	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01D8	CAN2IDAR4	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01D9	CAN2IDAR5	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01DA	CAN2IDAR6	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01DB	CAN2IDAR7	Read: Write:	AC7	AC6	AC5	AC4	AC3	AC2	AC1	AC0
$01DC	CAN2IDMR4	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01DD	CAN2IDMR5	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01DE	CAN2IDMR6	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01DF	CAN2IDMR7	Read: Write:	AM7	AM6	AM5	AM4	AM3	AM2	AM1	AM0
$01E0 - $01EF	CAN2RXFG	Read:	FOREGROUND RECEIVE BUFFER see **Table 1-2**							
		Write:								
$01F0 - $01FF	CAN2TXFG	Read: Write:	FOREGROUND TRANSMIT BUFFER see **Table 1-2**							

Section 2 Signal Description

This section describes signals that connect off-chip. It includes a pinout diagram, a table of signal properties, and detailed discussion of signals. It is built from the signal description sections of the Block User Guides of the individual IP blocks on the device.

2.1 Device Pinout

The MC9S12DP256B/MC9S12DT256/MC9S12DJ256 and MC9S12DG256 is available in a 112-pin low profile quad flat pack (LQFP) and MC9S12DJ256 is also available in a 80-pin quad flat pack (QFP). Most pins perform two or more functions, as described in the Signal Descriptions. **Figure 2-1** and **Figure 2-3** show the pin assignments.

Table 2-2 MC9S12DP256 Power and Ground Connection Summary

Mnemonic	Pin Number 112-pin QFP	Nominal Voltage	Description
$V_{DD1, 2}$	13, 65	2.5 V	Internal power and ground generated by internal regulator
$V_{SS1, 2}$	14, 66	0V	
V_{DDR}	41	5.0 V	External power and ground, supply to pin drivers and internal voltage regulator.
V_{SSR}	40	0 V	
V_{DDX}	107	5.0 V	External power and ground, supply to pin drivers.
V_{SSX}	106	0 V	
V_{DDA}	83	5.0 V	Operating voltage and ground for the analog-to-digital converters and the reference for the internal voltage regulator, allows the supply voltage to the A/D to be bypassed independently.
V_{SSA}	86	0 V	
V_{RL}	85	0 V	Reference voltages for the analog-to-digital converter.
V_{RH}	84	5.0 V	
V_{DDPLL}	43	2.5 V	Provides operating voltage and ground for the Phased-Locked Loop. This allows the supply voltage to the PLL to be bypassed independently. Internal power and ground generated by internal regulator.
V_{SSPLL}	45	0 V	
VREGEN	97	5V	Internal Voltage Regulator enable/disable

2.4.7 VREGEN — On Chip Voltage Regulator Enable

Enables the internal 5V to 2.5V voltage regulator. If this pin is tied low, VDD1,2 and VDDPLL must be supplied externally.

Section 6 HCS12 Core Block Description

Consult the HCS12 Core User Guide for information about the HCS12 core modules, i.e. central processing unit (CPU), interrupt module (INT), module mapping control module (MMC), multiplexed external bus interface (MEBI), breakpoint module (BKP) and background debug mode module (BDM).

Table 6-1 Configuration of HCS12 Core

Name	Description	MC9S12DP256B Configuration
PUCR_RESET	PUCR reset state	$90
NUM_INT	Interrupt Request Bus Width	56
INITEE_RST	INITEE reset state	$01
INITEE_WOK	INITEE Write anytime in normal mode	INITEE register is writeable once in normal modes
PPAGE_SMOD_ONLY	PPAGE Write only in special mode	PPAGE register is writable in all modes,reset state of the PPAGE register is $00

Section 7 Clock and Reset Generator (CRG) Block Description

Consult the CRG Block User Guide for information about the Clock and Reset Generator module.

7.1 Device-specific information

7.1.1 $\overline{\text{XCLKS}}$

The $\overline{\text{XCLKS}}$ input signal is active low (see **2.3.13 PE7 / NOACC / XCLKS — Port E I/O Pin 7**).

Section 8 Enhanced Capture Timer (ECT) Block Description

Consult the ECT_16B8C Block User Guide for information about the Enhanced Capture Timer module.

Section 9 Analog to Digital Converter (ATD) Block Description

There are two Analog to Digital Converters (ATD1 and ATD0) implemented on the MC9S12DP256B. Consult the ATD_10B8C Block User Guide for information about each Analog to Digital Converter module.

Section 10 Inter-IC Bus (IIC) Block Description

Consult the IIC Block User Guide for information about the Inter-IC Bus module.

Section 11 Serial Communications Interface (SCI) Block Description

There are two Serial Communications Interfaces (SCI1 and SCI0) implemented on the MC9S12DP256B device. Consult the SCI Block User Guide for information about each Serial Communications Interface module.

Section 12 Serial Peripheral Interface (SPI) Block Description

There are three Serial Peripheral Interfaces(SPI2, SPI1 and SPI0) implemented on MC9S12DP256B. Consult the SPI Block User Guide for information about each Serial Peripheral Interface module.

Section 13 J1850 (BDLC) Block Description

Consult the BDLC Block User Guide for information about the J1850 module.

Section 14 Pulse Width Modulator (PWM) Block Description

Consult the PWM_8B8C Block User Guide for information about the Pulse Width Modulator module.

Section 15 Flash EEPROM 256K Block Description

Consult the FTS256K Block User Guide for information about the flash module.

Section 16 EEPROM 4K Block Description

Consult the EETS4K Block User Guide for information about the EEPROM module.

Section 17 RAM Block Description

- Every supply pair must be decoupled by a ceramic capacitor connected as near as possible to the corresponding pins(C1 - C6).
- Central point of the ground star should be the VSSR pin.
- Use low ohmic low inductance connections between VSS1, VSS2 and VSSR.
- VSSPLL must be directly connected to VSSR.
- Keep traces of VSSPLL, EXTAL and XTAL as short as possible and occupied board area for C7, C8, C11 and Q1 as small as possible.
- Do not place other signals or supplies underneath area occupied by C7, C8, C10 and Q1 and the connection area to the MCU.
- Central power input should be fed in at the VDDA/VSSA pins.

A.1.7 Operating Conditions

This chapter describes the operating conditions of the device. Unless otherwise noted those conditions apply to all the following data.

NOTE: *Please refer to the temperature rating of the device (C, V, M) with regards to the ambient temperature T_A and the junction temperature T_J. For power dissipation calculations refer to* ***Section A.1.8 Power Dissipation and Thermal Characteristics****.*

Table A-4 Operating Conditions

Rating	Symbol	Min	Typ	Max	Unit
I/O, Regulator and Analog Supply Voltage	V_{DD5}	4.5	5	5.25	V
Digital Logic Supply Voltage [1]	V_{DD}	2.35	2.5	2.75	V
PLL Supply Voltage [2]	V_{DDPLL}	2.35	2.5	2.75	V
Voltage Difference VDDX to VDDR and VDDA	Δ_{VDDX}	-0.1	0	0.1	V
Voltage Difference VSSX to VSSR and VSSA	Δ_{VSSX}	-0.1	0	0.1	V
Oscillator	f_{osc}	0.5	-	16	MHz
Bus Frequency	f_{bus}	0.5	-	25	MHz
MC9S12DP256B**C**					
Operating Junction Temperature Range	T_J	-40	-	100	°C
Operating Ambient Temperature Range [2]	T_A	-40	27	85	°C
MC9S12DP256B**V**					
Operating Junction Temperature Range	T_J	-40	-	120	°C
Operating Ambient Temperature Range [2]	T_A	-40	27	105	°C
MC9S12DP256B**M**					
Operating Junction Temperature Range	T_J	-40	-	140	°C
Operating Ambient Temperature Range [2]	T_A	-40	27	125	°C

NOTES:
1. The device contains an internal voltage regulator to generate the logic and PLL supply out of the I/O supply. The absolute maximum ratings apply when this regulator is disabled and the device is powered from an external source.
2. Please refer to **Section A.1.8 Power Dissipation and Thermal Characteristics** for more details about the relation between ambient temperature T_A and device junction temperature T_J.

A.1.8 Power Dissipation and Thermal Characteristics

Power dissipation and thermal characteristics are closely related. The user must assure that the maximum operating junction temperature is not exceeded. The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \bullet \Theta_{JA})$$

T_J = Junction Temperature, [°C]

T_A = Ambient Temperature, [°C]

P_D = Total Chip Power Dissipation, [W]

Θ_{JA} = Package Thermal Resistance, [°C/W]

The total power dissipation can be calculated from:

$$P_D = P_{INT} + P_{IO}$$

P_{INT} = Chip Internal Power Dissipation, [W]

Two cases with internal voltage regulator enabled and disabled must be considered:

1. Internal Voltage Regulator disabled

$$P_{INT} = I_{DD} \cdot V_{DD} + I_{DDPLL} \cdot V_{DDPLL} + I_{DDA} \cdot V_{DDA}$$

$$P_{IO} = \sum_i R_{DSON} \cdot I_{IO_i}^2$$

P_{IO} is the sum of all output currents on I/O ports associated with VDDX and VDDR.

For R_{DSON} is valid:

$$R_{DSON} = \frac{V_{OL}}{I_{OL}}; \text{for outputs driven low}$$

respectively

$$R_{DSON} = \frac{V_{DD5} - V_{OH}}{I_{OH}}; \text{for outputs driven high}$$

2. Internal voltage regulator enabled

$$P_{INT} = I_{DDR} \cdot V_{DDR} + I_{DDA} \cdot V_{DDA}$$

I_{DDR} is the current shown in **Table A-7** and not the overall current flowing into VDDR, which additionally contains the current flowing into the external loads with output high.

$$P_{IO} = \sum_i R_{DSON} \cdot I_{IO_i}^2$$

P_{IO} is the sum of all output currents on I/O ports associated with VDDX and VDDR.

A.3 NVM, Flash and EEPROM

NOTE: *Unless otherwise noted the abbreviation NVM (Non Volatile Memory) is used for both Flash and EEPROM.*

A.3.1 NVM timing

The time base for all NVM program or erase operations is derived from the oscillator. A minimum oscillator frequency f_{NVMOSC} is required for performing program or erase operations. The NVM modules do not have any means to monitor the frequency and will not prevent program or erase operation at frequencies above or below the specified minimum. Attempting to program or erase the NVM modules at a lower frequency a full program or erase transition is not assured.

The Flash and EEPROM program and erase operations are timed using a clock derived from the oscillator using the FCLKDIV and ECLKDIV registers respectively. The frequency of this clock must be set within the limits specified as f_{NVMOP}.

The minimum program and erase times shown in **Table A-11** are calculated for maximum f_{NVMOP} and maximum f_{bus}. The maximum times are calculated for minimum f_{NVMOP} and a f_{bus} of 2MHz.

A.3.1.1 Single Word Programming

The programming time for single word programming is dependant on the bus frequency as a well as on the frequency f_{NVMOP} and can be calculated according to the following formula.

$$t_{swpgm} = 9 \cdot \frac{1}{f_{NVMOP}} + 25 \cdot \frac{1}{f_{bus}}$$

A.3.1.2 Burst Programming

This applies only to the Flash where up to 32 words in a row can be programmed consecutively using burst programming by keeping the command pipeline filled. The time to program a consecutive word can be calculated as:

$$t_{bwpgm} = 4 \cdot \frac{1}{f_{NVMOP}} + 9 \cdot \frac{1}{f_{bus}}$$

The time to program a whole row is:

$$t_{brpgm} = t_{swpgm} + 31 \cdot t_{bwpgm}$$

Burst programming is more than 2 times faster than single word programming.

A.3.1.3 Sector Erase

Erasing a 512 byte Flash sector or a 4 byte EEPROM sector takes:

$$t_{era} \approx 4000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.4 Mass Erase

Erasing a NVM block takes:

$$t_{mass} \approx 20000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.5 Blank Check

The time it takes to perform a blank check on the Flash or EEPROM is dependant on the location of the first non-blank word starting at relative address zero. It takes one bus cycle per word to verify plus a setup of the command.

$$t_{check} \approx location \cdot t_{cyc} + 10 \cdot t_{cyc}$$

Table A-11 NVM Timing Characteristics

Conditions are shown in **Table A-4** unless otherwise noted							
Num	**C**	**Rating**	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	D	External Oscillator Clock	f_{NVMOSC}	0.5		50 [1]	MHz
2	D	Bus frequency for Programming or Erase Operations	f_{NVMBUS}	1			MHz
3	D	Operating Frequency	f_{NVMOP}	150		200	kHz
4	P	Single Word Programming Time	t_{swpgm}	46 [2]		74.5 [3]	µs
5	D	Flash Burst Programming consecutive word [4]	t_{bwpgm}	20.4 [2]		31 [3]	µs
6	D	Flash Burst Programming Time for 32 Words [4]	t_{brpgm}	678.4 [2]		1035.5 [3]	µs
7	P	Sector Erase Time	t_{era}	20 [5]		26.7 [3]	ms
8	P	Mass Erase Time	t_{mass}	100 [5]		133 [3]	ms
9	D	Blank Check Time Flash per block	t_{check}	11 [6]		32778 [7]	t_{cyc}
10	D	Blank Check Time EEPROM per block	t_{check}	11 [6]		2058 [7]	t_{cyc}

NOTES:
1. Restrictions for oscillator in crystal mode apply!
2. Minimum Programming times are achieved under maximum NVM operating frequency f_{NVMOP} and maximum bus frequency f_{bus}.

A.5.3 Phase Locked Loop

The oscillator provides the reference clock for the PLL. The PLL´s Voltage Controlled Oscillator (VCO) is also the system clock source in self clock mode.

A.5.3.1 XFC Component Selection

This section describes the selection of the XFC components to achieve a good filter characteristics.

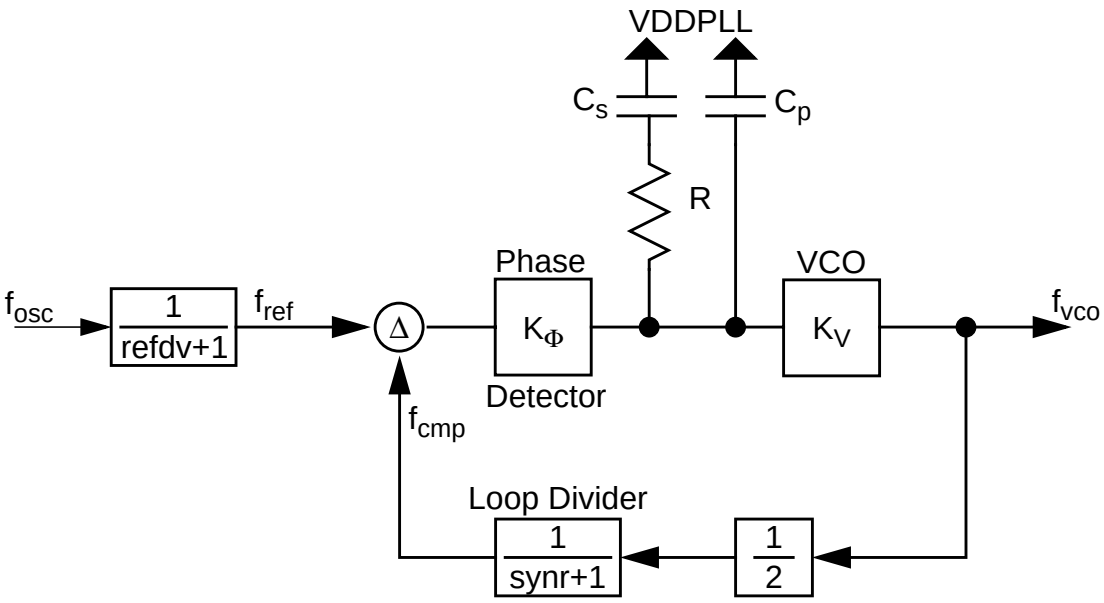


Figure A-2 Basic PLL functional diagram

The following procedure can be used to calculate the resistance and capacitance values using typical values for K_1, f_1 and i_{ch} from **Table A-16**.

The VCO Gain at the desired VCO output frequency is approximated by:

$$K_V = K_1 \cdot e^{\frac{(f_1 - f_{vco})}{K_1 \cdot 1V}}$$

The phase detector relationship is given by:

$$K_\Phi = -|i_{ch}| \cdot K_V$$

i_{ch} is the current in tracking mode.

A.6 MSCAN

Table A-17 MSCAN Wake-up Pulse Characteristics

Conditions are shown in **Table A-4** unless otherwise noted							
Num	**C**	**Rating**	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	P	MSCAN Wake-up dominant pulse filtered	t_{WUP}			2	µs
2	P	MSCAN Wake-up dominant pulse pass	t_{WUP}	5			µs

Table A-19 SPI Slave Mode Timing Characteristics

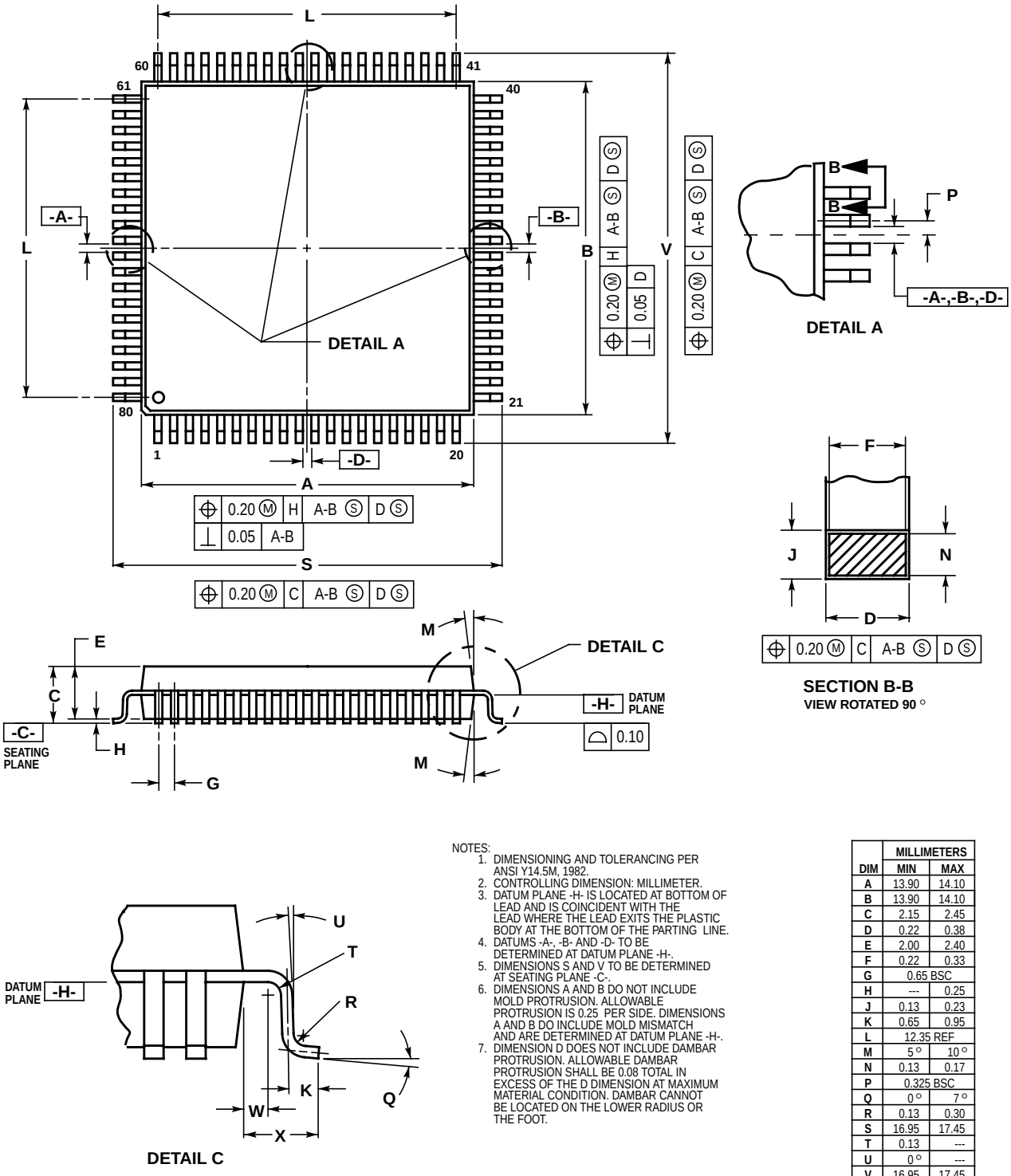
Conditions are shown in **Table A-4** unless otherwise noted, CLOAD = 200pF on all outputs							
Num	**C**	**Rating**	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	P	Operating Frequency	f_{op}	DC		1/4	f_{bus}
1	P	SCK Period $t_{sck} = 1./f_{op}$	t_{sck}	4		2048	t_{bus}
2	D	Enable Lead Time	t_{lead}	1			t_{cyc}
3	D	Enable Lag Time	t_{lag}	1			t_{cyc}
4	D	Clock (SCK) High or Low Time	t_{wsck}	$t_{cyc} – 30$			ns
5	D	Data Setup Time (Inputs)	t_{su}	25			ns
6	D	Data Hold Time (Inputs)	t_{hi}	25			ns
7	D	Slave Access Time	t_a			1	t_{cyc}
8	D	Slave MISO Disable Time	t_{dis}			1	t_{cyc}
9	D	Data Valid (after SCK Edge)	t_v			25	ns
10	D	Data Hold Time (Outputs)	t_{ho}	0			ns
11	D	Rise Time Inputs and Outputs	t_r			25	ns
12	D	Fall Time Inputs and Outputs	t_f			25	ns

Table A-20 Expanded Bus Timing Characteristics

Conditions are shown in **Table A-4** unless otherwise noted, C_{LOAD} = 50pF							
Num	**C**	**Rating**	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
32	D	NOACC hold time	t_{NOH}	2			ns
33	D	IPIPO[1:0] delay time	t_{P0D}	2		7	ns
34	D	IPIPO[1:0] valid time to E rise (PW_{EL}–t_{P0D})	t_{P0V}	11			ns
35	D	IPIPO[1:0] delay time[1] (PW_{EH}-t_{P1V})	t_{P1D}	2		25	ns
36	D	IPIPO[1:0] valid time to E fall	t_{P1V}	11			ns

NOTES:
1. Affected by clock stretch: add N x t_{cyc} where N=0,1,2 or 3, depending on the number of clock stretches.

B.3 80-pin QFP package



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DATUM PLANE -H- IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS -A-, -B- AND -D- TO BE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS S AND V TO BE DETERMINED AT SEATING PLANE -C-.
6. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS A AND B DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

	MILLIMETERS	
DIM	MIN	MAX
A	13.90	14.10
B	13.90	14.10
C	2.15	2.45
D	0.22	0.38
E	2.00	2.40
F	0.22	0.33
G	0.65 BSC	
H	---	0.25
J	0.13	0.23
K	0.65	0.95
L	12.35 REF	
M	5°	10°
N	0.13	0.17
P	0.325 BSC	
Q	0°	7°
R	0.13	0.30
S	16.95	17.45
T	0.13	---
U	0°	---
V	16.95	17.45
W	0.35	0.45
X	1.6 REF	

Figure B-2 80-pin QFP Mechanical Dimensions (case no. 841B)

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